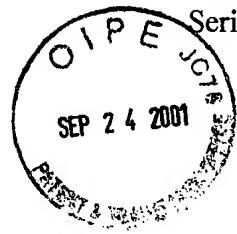


TSMC 98-262
Serial Number 09/325,951



PRELIMINARY AMENDMENT

*119/C
9/27/01
V. Varnals
USPTO MAIL ROOM
SEP 25 2001*

TO: COMMISSIONER OF PATENTS AND TRADEMARKS
Washington, D. C. 20231

FROM: George O. Saile (Reg. No. 19,572)
20 McIntosh Drive
Poughkeepsie, NY 12603

DATE: 17 September 2001

REF: APPLICANT : Chiang et al.
SERIAL NO. : 09/325,951
ART UNIT : 2812
FILING DATE : 04/06/99
ATTY NO. : TSMC 98-262
EXAMINER : R. Pompey
TITLE : Method for Forming High Purity Silicon Oxide Field
Oxide Isolation Region

Sir:

In response to an advisory action mailed on 07 August 2001, please consider the following amendments and remarks pertaining to the above referenced application.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as First Class mail in an envelope addressed to the Commissioner of Patents and Trademarks, Washington, D. C. 20231 on 21 September 2001

Stephen B. Aterman
Name Reg #37,761

JSB
Signature

9/21/01
Date